

STD20NF10

N-channel 100V - 0.038Ω - 100A - DPAK Low gate charge STripFETTM II Power MOSFET

Features

Туре	V _{DSS}	R _{DS(on)}	I _D
STD20NF10	100V	<0.045Ω	25A ⁽¹⁾

- 1. Current limited by package
- Exceptional dv/dt capability
- Application oriented characterization

Description

This MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced highefficiency, high-frequency isolated DC-DC converters for Telecom and Computer applications. It is also intended for any applications with low gate drive requirements.



■ Switching applications

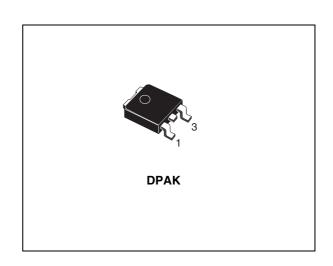


Figure 1. Internal schematic diagram

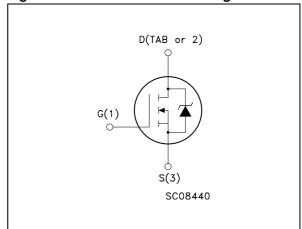


Table 1. Device summary

Part number	Marking	Package	Packaging
STD20NF10T4	D20NF10	DPAK	Tape & reel

Contents STD20NF10

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STD20NF10 Electrical ratings

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit	
V _{DS}	Drain-source voltage (V _{GS} = 0)	100	V	
V _{DGR}	Drain-gate voltage (R_{GS} = 20 kΩ)	100	V	
V _{GS}	Gate- source voltage	± 20	V	
I _D ⁽¹⁾	Drain current (continuous) at T _C = 25°C	25	Α	
I _D	Drain current (continuous) at T _C = 100°C	21	Α	
I _{DM} ⁽²⁾	Drain current (pulsed)	100	А	
P _{tot}	P _{tot} Total dissipation at T _C = 25°C		W	
	Derating Factor		W/°C	
dv/dt ⁽³⁾	Peak diode recovery avalanche energy	20	V/ns	
E _{AS} (4)	Single pulse avalanche energy	300	mJ	
T _{stg}	g Storage temperature		°C	
Tj	Max. operating junction temperature	55 to 175		

- 1. Current limited by package
- 2. Pulse width limited by safe operating area.
- 3. I_{SD} 25A, di/dt \leq 300A/ μ s, V_{DD} = $V_{(BR)DSS}$, $T_j \leq T_{JMAX}$
- 4. Starting $T_i = 25$ °C, $I_D = 10A$, $V_{DD} = 27V$

Table 3. Thermal data

Rthj-case	Thermal resistance junction-case max	1.76	°C/W
Rthj-amb	nb Thermal resistance junction-ambient max		°C/W
TJ	T _J Maximum lead temperature for soldering purpose		°C

Electrical characteristics STD20NF10

2 Electrical characteristics

(T_{CASE} =25°C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	100			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V_{DS} = Max rating V_{DS} = Max rating, T_{C} = 125°C			1 10	μ Α μ Α
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ± 20V			±100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	3	4	V
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10V, I _D = 15A		0.038	0.045	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
9 _{fs} ⁽¹⁾	Forward transconductance	$V_{DS} = 15V_{,} I_{D} = 15A$		10		S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V, f = 1MHz,$ $V_{GS} = 0$		1200 180 80		pF pF pF
t _{d(on)} t _r t _{d(off)} t _f	Turn-on delay time Rise time Turn-off delay time Fall time	V_{DD} = 50V, I_{D} = 15A R_{G} = 4.7 Ω V_{GS} = 10V (see <i>Figure 14</i>)		15 40 45 10		ns ns ns
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 80V, I_D = 30A, V_{GS} = 10V, R_G = 4.7 Ω (see <i>Figure 15</i>)		40 8 15	55	nC nC nC

^{1.} Pulsed: Pulse duration = 300 μ s, duty cycle 1.5%.

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SD}	Source-drain current Source-drain current (pulsed)				30 120	A A
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} = 20A, V _{GS} = 0			1.3	V
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 30A$, di/dt = 100A/ μ s, $V_{DD} = 55V$, $T_j = 150$ °C (see <i>Figure 16</i>)		110 390 7.5		ns μC A

^{1.} Pulse width limited by safe operating area.

^{2.} Pulsed: Pulse duration = 300 μ s, duty cycle 1.5%

Electrical characteristics STD20NF10

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Thermal impedance

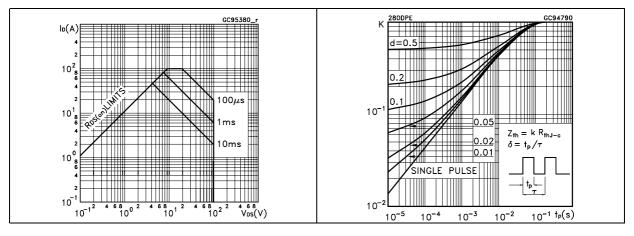


Figure 4. Output characteristics

Figure 5. Transfer characteristics

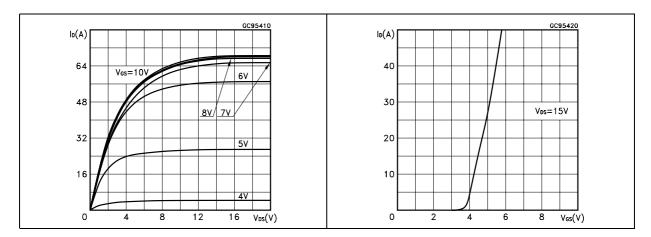


Figure 6. Transconductance

Figure 7. Static drain-source on resistance

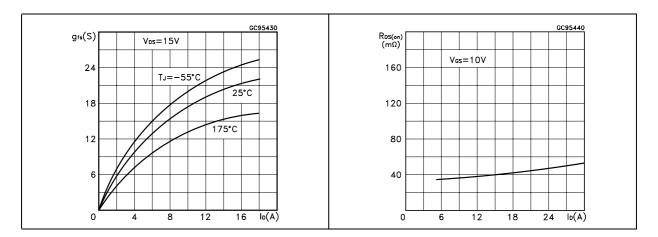


Figure 8. Gate charge vs. gate-source voltage Figure 9. Capacitance variations

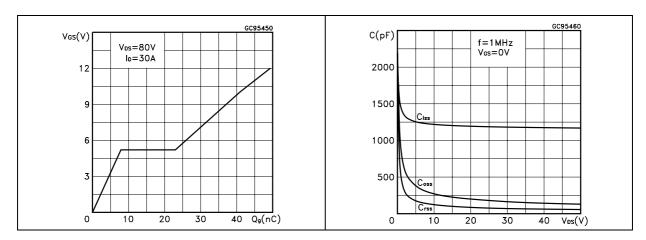


Figure 10. Normalized gate threshold voltage vs. temperature

Figure 11. Normalized on resistance vs. temperature

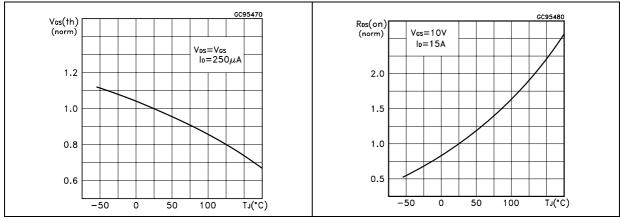
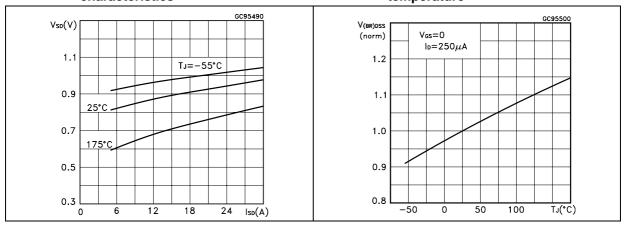


Figure 12. Source-drain diode forward characteristics

Figure 13. Normalized breakdown voltage vs. temperature



Test circuit STD20NF10

3 Test circuit

Figure 14. Switching times test circuit for resistive load

Figure 15. Gate charge test circuit

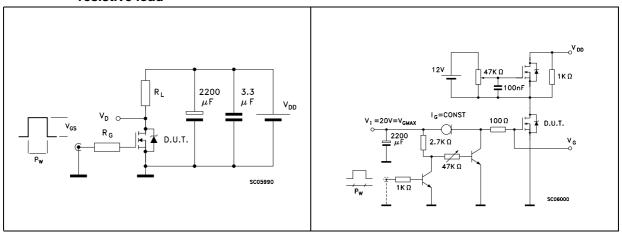


Figure 16. Test circuit for inductive load switching and diode recovery times

Figure 17. Unclamped Inductive load test circuit

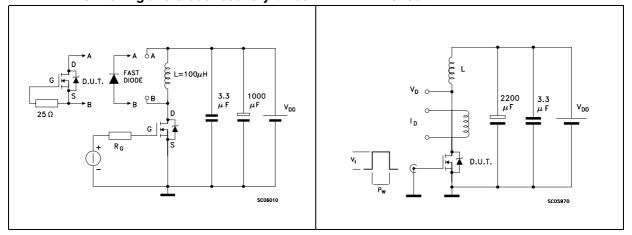
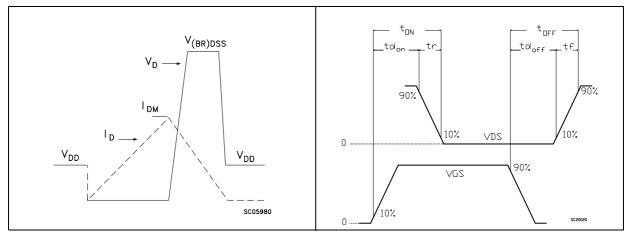


Figure 18. Unclamped inductive waveform

Figure 19. Switching time waveform



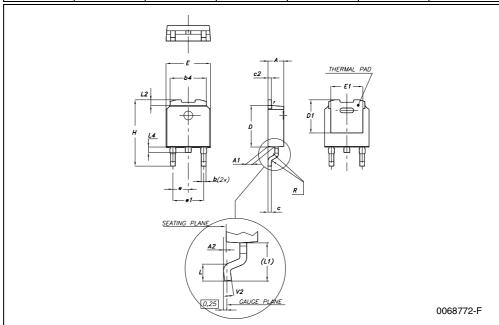
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

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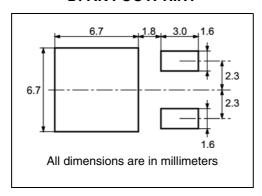
DPAK MECHANICAL DATA

DIM		mm.				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	2.2		2.4	0.086		0.094
A1	0.9		1,1	0.035		0.043
A2	0.03		0.23	0.001		0.009
В	0.64		0.9	0.025		0.035
b4	5.2		5.4	0.204		0.212
С	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
D1		5.1			0.200	
E	6.4		6.6	0.252		0.260
E1		4.7			0.185	
е		2.28			0.090	
e1	4.4		4.6	0.173		0.181
Н	9.35		10.1	0.368		0.397
L	1			0.039		
(L1)		2.8			0.110	
L2		0.8			0.031	
L4	0.6		1	0.023		0.039
R		0.2			0.008	
V2	0°		8°	0°		8°

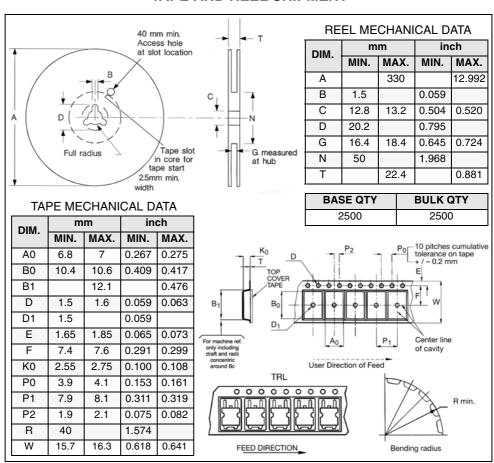


5 Packing mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT



Revision history STD20NF10

6 Revision history

Table 7. Revision history

	Date	Revision	Changes
	21-Jun-2004	3	Preliminary datasheet
	03-Jul-2006	4	New template, no content change
Ī	13-Aug-2007	5	Updated marking on <i>Table 1</i>

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